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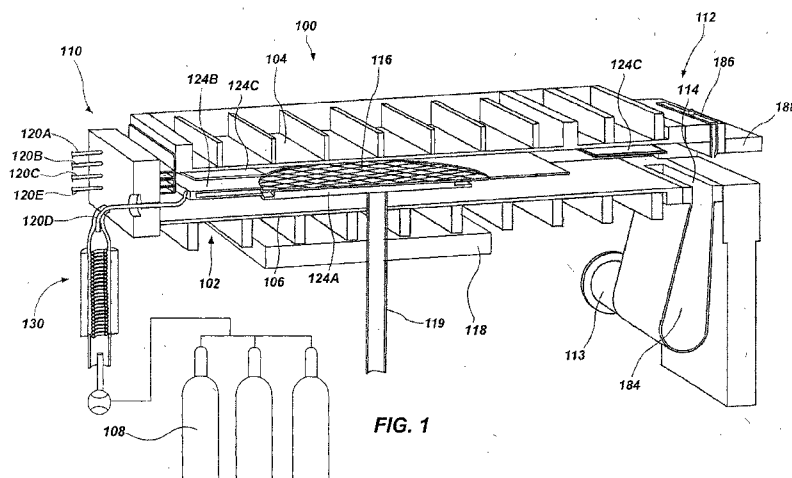


FIG. 1

(57) Abstract: Processes and systems are used to reduce undesired deposits within a reaction chamber associated with a semiconductor deposition system. A cleaning gas may be caused to flow through at least one gas flow path extending through at least one gas furnace, and the heated cleaning gas may be introduced into a reaction chamber to remove at least a portion of undesired deposits from within the reaction chamber.